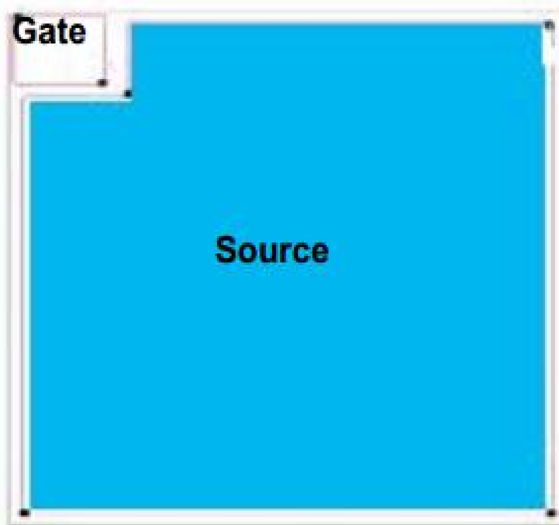
GWM8205 Wafer Information

Date: 2018/7/26

Wafer Name	GWM8205
Wafer Diameter	8 inchs(±0.1 inchs)
Die Size	740um * 500um
Scribe Line Width	60um
Wafer Thichness	8 mil(±0.6 mil)
Metalization(Back Side)	Ti/ Ni/ Ag
Metal Thickness(Back Side)	1.4um
Metalization(Front Side)	Al/ Cu
Metal Thickness (Front side)	4 um



- Bonding Area:
  Gate:160 μm x 160 μm.
  Source: Full metalized surface of source region
- Recommended Wire Bounding
  Gate: 2milx1Au
  Source: 2milx3 Au